

Art Unit: ***

28. A single crystal gallium nitride substrate according to Claim 27, wherein a direction of a shortest repetition pitch which is equal to a shorter side of the equivalent rectangles or a shorter orthogonal line of the lozenge of the two-fold rotation symmetry pattern is either a <1-100> direction or a <11-20> direction.
29. A single crystal gallium nitride substrate according to Claim 22, wherein a shortest repetition pitch of the closed defect accumulating regions (H) ranges from $50 \mu m$ to $2000 \mu m$ on the surface regularly and periodically provided with the fundamental units (Q).
30. A single crystal gallium nitride substrate according to Claim 2, wherein the closed defect accumulating regions (H) extend in a c-axis direction and penetrate the substrate crystal.

CLAIMS 31-72 CANCELLED